2-input NAND gate; open drain Rev. 6 — 2 July 2012

Product data sheet

1. **General description**

The 74LVC1G38 provides a 2-input NAND function.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of this device as translator in a mixed 3.3 V and 5 V environment.

This device is fully specified for partial power-down applications using IOFF. The IOFF circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

Features and benefits 2.

- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant outputs for interfacing with 5 V logic
- High noise immunity
- Complies with JEDEC standard:
 - JESD8-7 (1.65 V to 1.95 V)
 - JESD8-5 (2.3 V to 2.7 V)
 - JESD8-B/JESD36 (2.7 V to 3.6 V).
- ESD protection:
 - HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V
- ± 24 mA output drive (V_{CC} = 3.0 V)
- CMOS low power consumption
- Open drain outputs
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5 V
- Multiple package options
- Specified from –40 °C to +125 °C.



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3. Ordering information

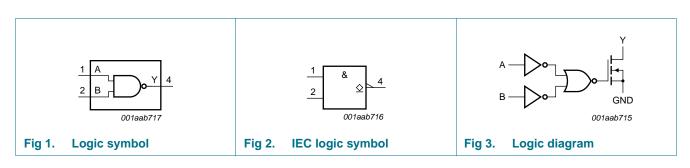
Type number	Package			
	Temperature range	Name	Description	Version
74LVC1G38GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1
74LVC1G38GV	–40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753
74LVC1G38GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1.45 \times 0.5 mm	SOT886
74LVC1G38GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1 \times 0.5 mm	SOT891
74LVC1G38GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm	SOT1115
74LVC1G38GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $1.0 \times 1.0 \times 0.35$ mm	SOT1202
74LVC1G38GX	–40 °C to +125 °C	X2SON5	X2SON5: plastic thermal enhanced extremely thin small outline package; no leads; 5 terminals; body $0.8 \times 0.8 \times 0.35$ mm	SOT1226

4. Marking

Table 2. Marking	
Type number	Marking code ^[1]
74LVC1G38GW	YB
74LVC1G38GV	YB
74LVC1G38GM	YB
74LVC1G38GF	YB
74LVC1G38GN	YB
74LVC1G38GS	YB
74LVC1G38GX	YB

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

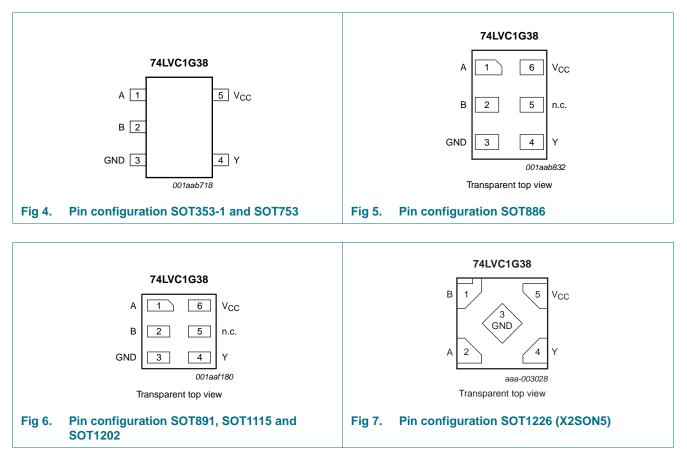
5. Functional diagram



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6. Pinning information

6.1 Pinning



6.2 Pin description

Symbol	Pin		Description
-,	TSSOP5 and X2SON5	XSON6	
A	1	1	data input
В	2	2	data input
GND	3	3	ground (0 V)
Y	4	4	data output
n.c.	•	5	not connected
V _{CC}	5	6	supply voltage

7. Functional description

Table 4.	Function table ^[1]		
Input			Output
Α		В	Y
L		L	Z
L		Н	Z
Н		L	Z
Н		Н	L

[1] H = HIGH voltage level; L = LOW voltage level; Z = high-impedance OFF state

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+6.5	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+6.5	V
I _{OK}	output clamping current	$V_{\rm O}$ > $V_{\rm CC}$ or $V_{\rm O}$ < 0 V	-	±50	mA
Vo	output voltage	Active mode	<u>[1][2]</u> –0.5	+6.5	V
		Power-down mode	<u>[1][2]</u> –0.5	+6.5	V
lo	output current	$V_{O} = 0 V$ to V_{CC}	-	±50	mA
I _{CC}	supply current		-	100	mA
I _{GND}	ground current		-100	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \ to +125 \ ^{\circ}C$	<u>[3]</u> _	300	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] When $V_{CC} = 0 V$ (Power-down mode), the output voltage can be 5.5 V in normal operation.

[3] For TSSOP5 and SC-74A packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K. For XSON6 and X2SON 5packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

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Recommended operating conditions 9.

Table 6.	Recommended operating	ng conditions				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CC}	supply voltage		1.65	-	5.5	V
VI	input voltage		0	-	5.5	V
Vo	output voltage	Active mode	0	-	5.5	V
		Disable mode; V_{CC} = 1.65 V to 5.5 V	0	-	5.5	V
		Power-down mode; $V_{CC} = 0 V$	0	-	5.5	V
T _{amb}	ambient temperature		-40	-	+125	°C
$\Delta t / \Delta V$	input transition rise and	V_{CC} = 1.65 V to 2.7 V	-	-	20	ns/V
	fall rate	V _{CC} = 2.7 V to 5.5 V	-	-	10	ns/V

10. Static characteristics

Table 7. **Static characteristics**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = -	40 °C to +85 °C <u>[1]</u>					
V _{IH}	HIGH-level input voltage	$V_{CC} = 1.65 \text{ V}$ to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.7	-	-	V
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	2.0	-	-	V
		V_{CC} = 4.5 V to 5.5 V	$0.7\times V_{CC}$	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 1.65 V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V_{CC} = 2.7 V to 3.6 V	-	-	0.8	V
		V_{CC} = 4.5 V to 5.5 V	-	-	$0.3 \times V_{CC}$	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$	-	-	-	
		I_O = 100 $\mu\text{A};V_{CC}$ = 1.65 V to 5.5 V	-	-	0.1	V
		$I_{O} = 4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.45	V
		I_{O} = 8 mA; V_{CC} = 2.3 V	-	-	0.3	V
		$I_0 = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	-	-	0.4	V
		$I_0 = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.55	V
		$I_0 = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.55	V
l _l	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	±0.1	±5	μΑ
I _{OZ}	OFF-state output current	$ V_{I} = V_{IH} \text{ or } V_{IL}; V_{O} = V_{CC} \text{ or } GND; $	-	±0.1	±10	μΑ
I _{OFF}	power-off leakage current	$V_{I} \text{ or } V_{O} = 5.5 \text{ V}; V_{CC} = 0 \text{ V}$	-	±0.1	±10	μΑ
I _{CC}	supply current	$V_{I} = 5.5 V \text{ or GND};$ $V_{CC} = 1.65 V \text{ to } 5.5 V; I_{O} = 0 \text{ A}$	-	0.1	10	μΑ
ΔI _{CC}	additional supply current		-	5	500	μΑ
CI	input capacitance		-	2.5	-	pF

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2-input NAND gate; open drain

At recom	mended operating condition	s; voltages are referenced to GND (ground	= 0 V).			
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} =	40 °C to +125 °C					
V _{IH}	HIGH-level input voltage	V_{CC} = 1.65 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.7	-	-	V
		$V_{CC} = 2.7 V \text{ to } 3.6 V$	2.0	-	-	V
		V_{CC} = 4.5 V to 5.5 V	$0.7\times V_{CC}$	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 1.65 V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	-	-	0.8	V
		V_{CC} = 4.5 V to 5.5 V	-	-	$0.3\times V_{CC}$	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$	-	-	-	
		I_O = 100 $\mu\text{A};V_{CC}$ = 1.65 V to 5.5 V	-	-	0.1	V
		$I_{O} = 4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.70	V
		$I_{O} = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		$I_0 = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	-	-	0.60	V
		$I_0 = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.80	V
		$I_{O} = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.80	V
l	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	-	±100	μΑ
I _{OZ}	OFF-state output current		-	-	±200	μΑ
I _{OFF}	power-off leakage current	V_1 or V_0 = 5.5 V; V_{CC} = 0 V	-	-	±200	μΑ
I _{CC}	supply current	$V_{I} = 5.5 V \text{ or GND};$ $V_{CC} = 1.65 V \text{ to } 5.5 V; I_{O} = 0 \text{ A}$	-	-	200	μΑ
Δl _{CC}	additional supply current	$V_{I} = V_{CC} - 0.6 \text{ V}; I_{O} = 0 \text{ A};$ $V_{CC} = 2.3 \text{ V}$ to 5.5 V; per pin	-	-	5000	μΑ

Table 7. Static characteristics ... continued

[1] All typical values are measured at V_{CC} = 3.3 V and T_{amb} = 25 °C.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V). For test circuit see Figure 9.

Symbol	Parameter	Conditions	-40) °C to +85	S°C	-40 °C to	o +125 ℃	Unit
			Min	Typ <mark>[1]</mark>	Max	Min	Max	
t _{pd}	propagation delay	A, B to Y; see Figure 8						
		V_{CC} = 1.65 V to 1.95 V	1.0	3.0	10.0	1.0	12.5	ns
		V_{CC} = 2.3 V to 2.7 V	0.5	1.8	6.0	0.5	7.5	ns
		$V_{CC} = 2.7 V$	0.5	2.5	5.0	0.5	6.5	ns
		V_{CC} = 3.0 V to 3.6 V	0.5	2.3	4.5	0.5	5.7	ns
		V_{CC} = 4.5 V to 5.5 V	0.5	1.5	3.9	0.5	4.9	ns
C_{PD}	power dissipation capacitance	$V_{CC} = 3.3 \text{ V};$ $V_{I} = \text{GND to } V_{CC}$	-	6	-	-	-	pF

[1] Typical values are measured at T_{amb} = 25 °C and V_{CC} = 1.8 V, 2.5 V, 2.7 V, 3.3 V and 5.0 V respectively.

 $\label{eq:tpd} [2] \quad t_{pd} \text{ is the same as } t_{PZL} \text{ and } t_{PLZ}.$

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \sum (C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$

 f_i = input frequency in MHz;

 $f_o =$ output frequency in MHz;

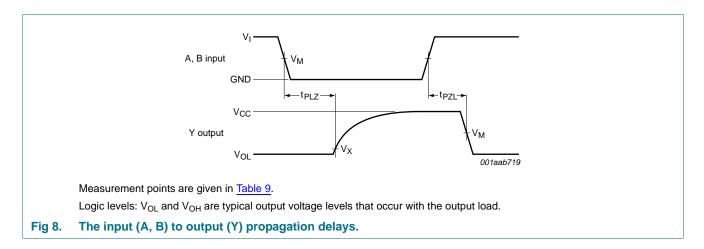
 C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

12. AC waveforms

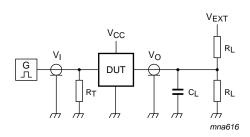


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Table 9. Measurement	ent points		
Supply voltage	Input	Output	
V _{CC}	V _M	V _M	V _X
1.65 V to 1.95 V	$0.5\times V_{CC}$	$0.5 imes V_{CC}$	V _{OL} + 0.15 V
2.3 V to 2.7 V	$0.5 imes V_{CC}$	$0.5\times V_{CC}$	V _{OL} + 0.15 V
2.7 V	1.5 V	1.5 V	V _{OL} + 0.3 V
3.0 V to 3.6 V	1.5 V	1.5 V	V _{OL} + 0.3 V
4.5 V to 5.5 V	$0.5 imes V_{CC}$	$0.5 imes V_{CC}$	V _{OL} + 0.3 V



Test data is given in Table 10.

Definitions for test circuit:

R_L = Load resistance.

 C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to the output impedance Z_0 of the pulse generator.

 V_{EXT} = External voltage for measuring switching times.

Fig 9. Test circuit for measuring switching times

Table 10. Test data

Supply voltage	Input		Load		V _{EXT}
V _{CC}	VI	t _r , t _f	CL	RL	t _{PLH} , t _{PHL}
1.65 V to 1.95 V	V _{CC}	\leq 2.0 ns	30 pF	1 kΩ	open
2.3 V to 2.7 V	V _{CC}	\leq 2.0 ns	30 pF	500 Ω	open
2.7 V	2.7 V	\leq 2.5 ns	50 pF	500 Ω	open
3.0 V to 3.6 V	2.7 V	\leq 2.5 ns	50 pF	500 Ω	open
4.5 V to 5.5 V	V _{CC}	\leq 2.5 ns	50 pF	500 Ω	open

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13. Package outline

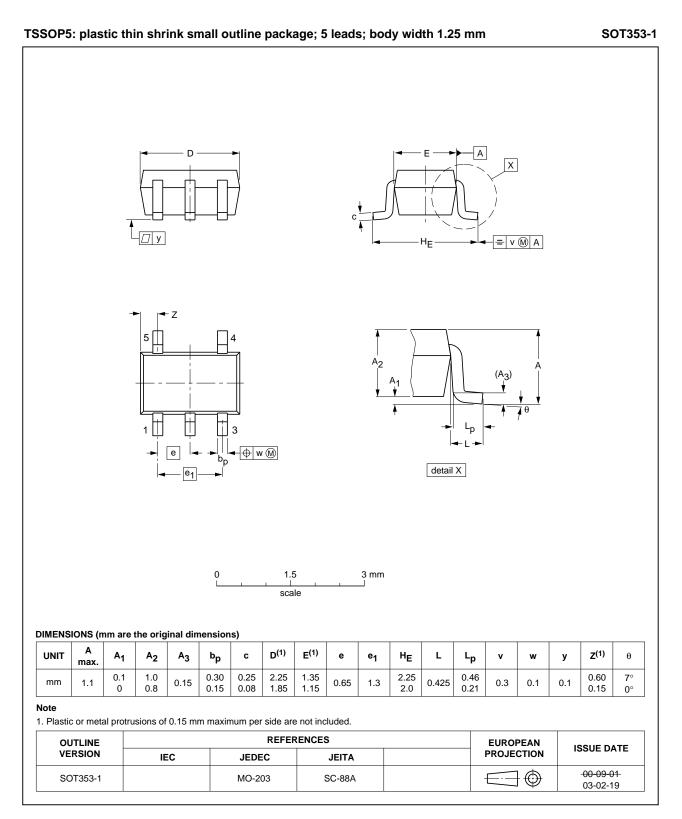
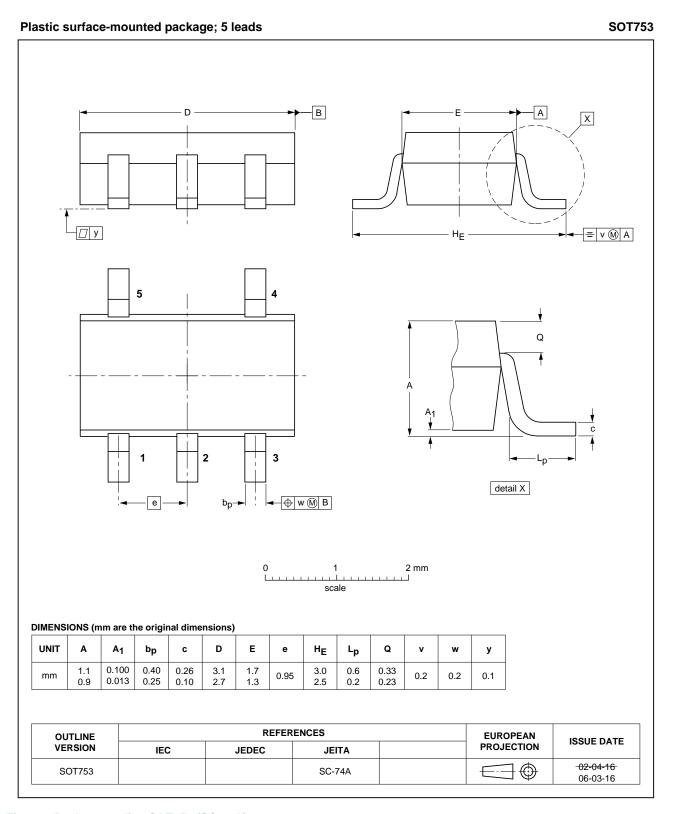


Fig 10. Package outline SOT353-1 (TSSOP5)

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Fig 11. Package outline SOT753 (SC-74A)
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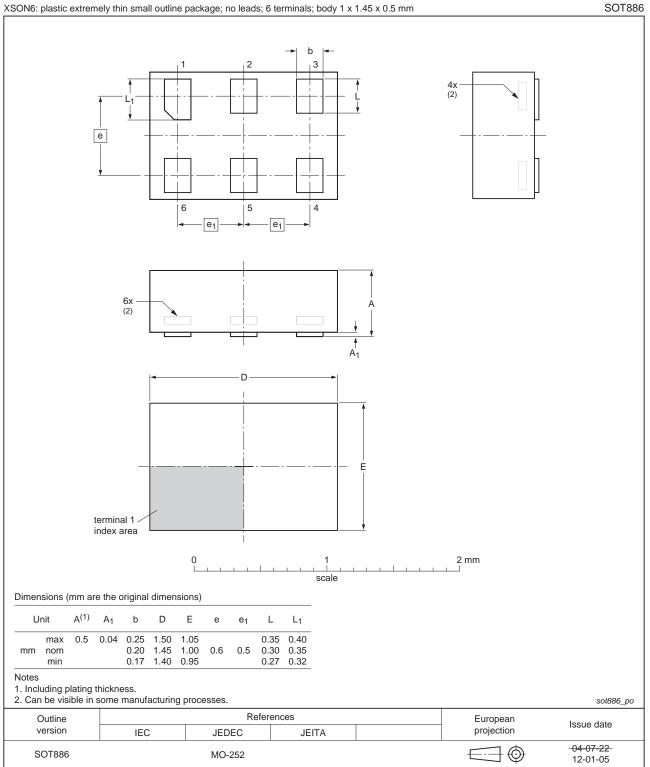


Fig 12. Package outline SOT886 (XSON6)

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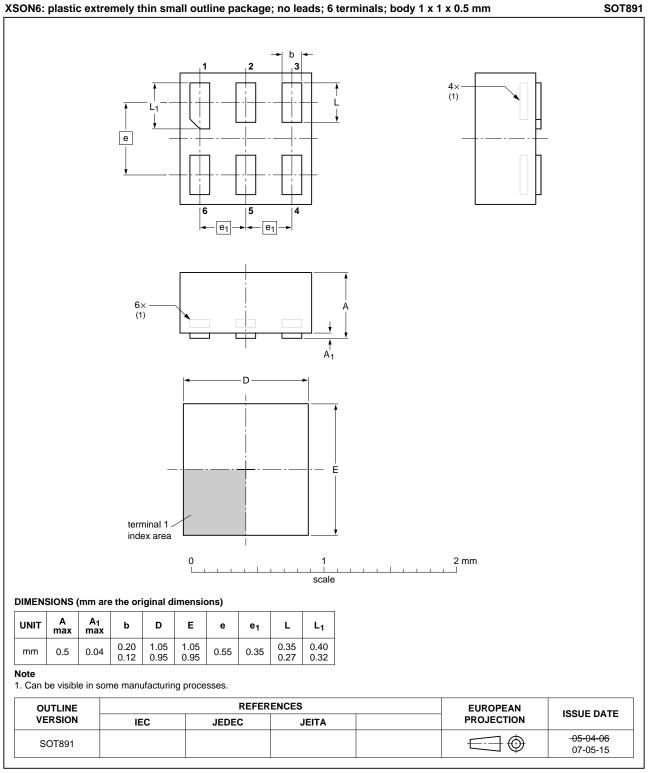
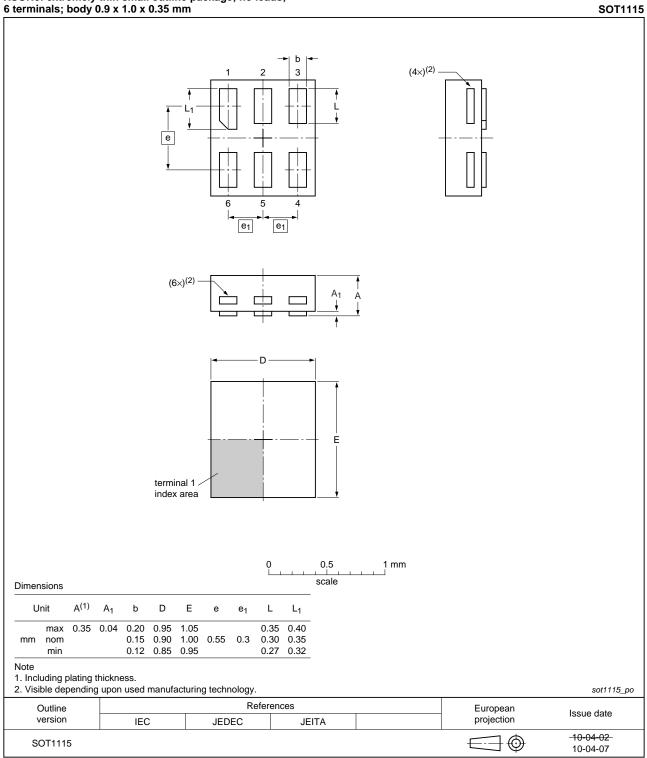


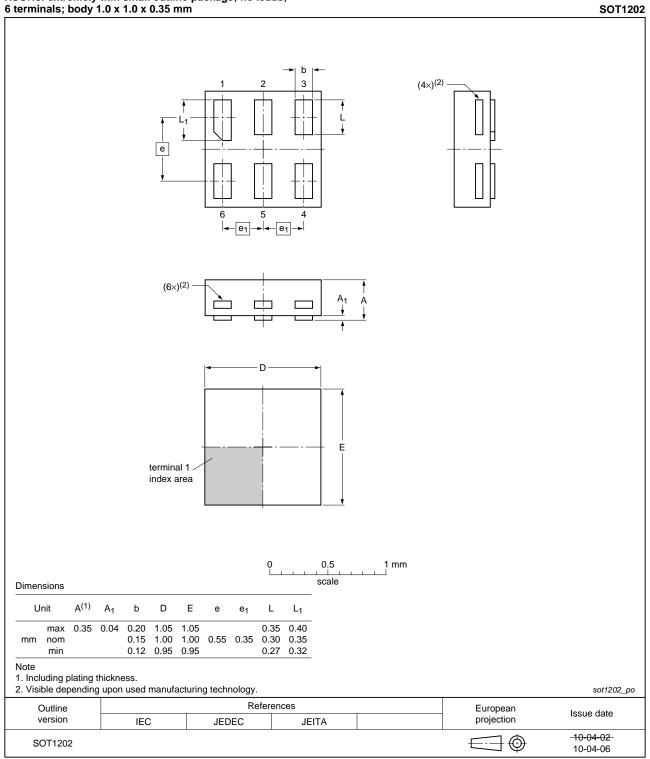
Fig 13. Package outline SOT891 (XSON6)



XSON6: extremely thin small outline package; no leads; 6 terminals; body 0.9 x 1.0 x 0.35 mm

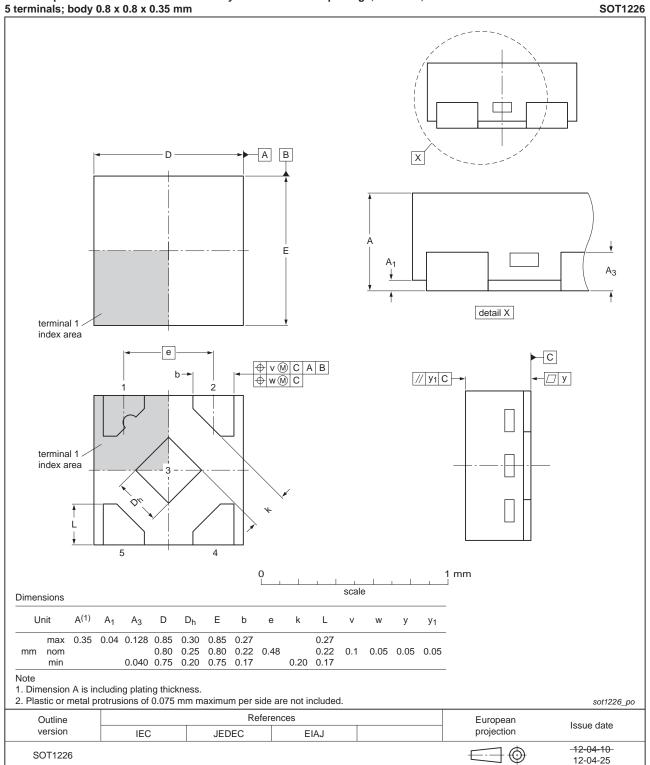
Fig 14. Package outline SOT1115 (XSON6)

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XSON6: extremely thin small outline package; no leads; 6 terminals; body 1.0 x 1.0 x 0.35 mm

Fig 15. Package outline SOT1202 (XSON6)



X2SON5: plastic thermal enhanced extremely thin small outline package; no leads; 5 terminals; body 0.8 x 0.8 x 0.35 mm

Fig 16. Package outline SOT1226 (X2SON5)

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14. Abbreviations

Acronym CMOS DUT ESD HBM	Description Complementary Metal Oxide Semiconductor Device Under Test
DUT ESD	· · ·
ESD	Device Under Test
LIDM	ElectroStatic Discharge
TIDIVI	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 12. Revision history					
Document ID	Release date	Data sheet status	Change notice	Supersedes	
74LVC1G38 v.6	20120702	Product data sheet	-	74LVC1G38 v.5	
Modifications:	Added type number 74LVC1G38GX (SOT1226)				
	 Package outline 	e drawing of SOT886 (<u>Figure 12</u>) m	odified.		
74LVC1G38 v.5	20111206	Product data sheet	-	74LVC1G38 v.4	
Modifications:	Modifications: • Legal pages updated.				
74LVC1G38 v.4	20101005	Product data sheet	-	74LVC1G38 v.3	
74LVC1G38 v.3	20070827	Product data sheet	-	74LVC1G38 v.2	
74LVC1G38 v.2	20060913	Product data sheet	-	74LVC1G38 v.1	
74LVC1G38 v.1	20041018	Product data sheet	-	-	

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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16.4 Trademarks

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17. Contact information

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2-input NAND gate; open drain

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